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Electron beam induced flicker noise in carbon nanotubes JACK CHAN, BRIAN BURKE, UVA Physics, CHONG HU, JOE CAMPBELL, LLOYD HARRIOTT, Electrical and Computer Engineering, KEITH WILLIAMS, UVA Physics — Discrete current switching is induced in carbon nanotubes by low dosage electron beam irradiation. Switching is observed at room temperature. Switching is created by electron beam. Change in noise power spectral density following electron beam exposure will be discussed. The observed flicker noise is attributed to charge traps created by electron beam irradiation in silicon oxide.

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